

Printed Pages: 3

NEC-703

(Following Paper ID and Roll No. to be filled in your Answer Books)

Paper ID : 2012358

Roll No. 

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**B.TECH.**

Regular Theory Examination (Odd Sem-VII), 2016-17

**VLSI DESIGN**

Time : 3 Hours

Max. Marks : 100

**SECTION -A**

**1 Attempt all questions. All parts carry equal marks. Write answer of each part in short. (10×2=20)**

- a) What do you meant by threshold voltage of MOS transistor? Explain
- b) List the steps used for CMOS fabrication.
- c) Define delay time and discuss delay models.
- d) Name any two basic CAD tools and explain.
- e) Describe basic principle of pass transistor circuits.
- f) Write the importance low power in VLSI architectures.
- g) Bring out the drawbacks of dynamic logic.
- h) Distinguish between SRAM and DRAM.
- i) Classify adiabatic logic circuits.

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- j) Mention the scaling principles. What is the need for scaling.

SECTION - B

Note: Attempt any five questions from this section.

(5×10=50)

- Analyze the characteristics of CMOS inverter with neat sketch.
- What do you mean by Design for testability. Discuss scan based techniques.
- Narrate in detail about VLSI low power architectures with suitable diagram.
- Design an 8MB X 16 bit memory architecture using 512K X 8 bit memory chip.
- Explain the Ad Hoc testable design techniques with a suitable example.
- Illuminate the n-well CMOS fabrication process with neat diagrams.
- Analyze the different gate delay model of CMOS gate transistor.
- Differentiate between EEPROM and Flash memory.

SECTION - C

Note: Attempt any two questions from this section.

(2×15=30)

10. Implement a 2 input NAND gate using:  
a) Dynamic CMOS logic

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- b) Domino CMOS logic

- Derive the expression for total power dissipation of a CMOS circuit.
- Narrate in detail about the operation of NMOS transistor with different operating modes.

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